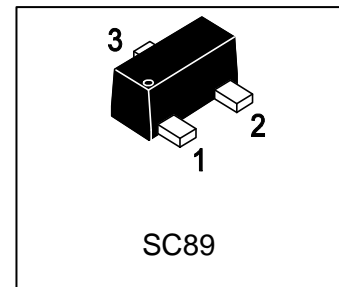


LRB715WT1G

Dual Series Schottky Barrier Diodes

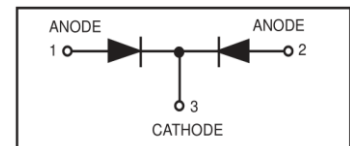
1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- Small surface mounting type.
- Low VF and low IR
- High reliability



2. DEVICE MARKING AND RESISTOR VALUES

Device	Marking	Shipping
LRB715WT1G	3D	3000/Tape&Reel
LRB715WT3G	3D	10000/Tape&Reel



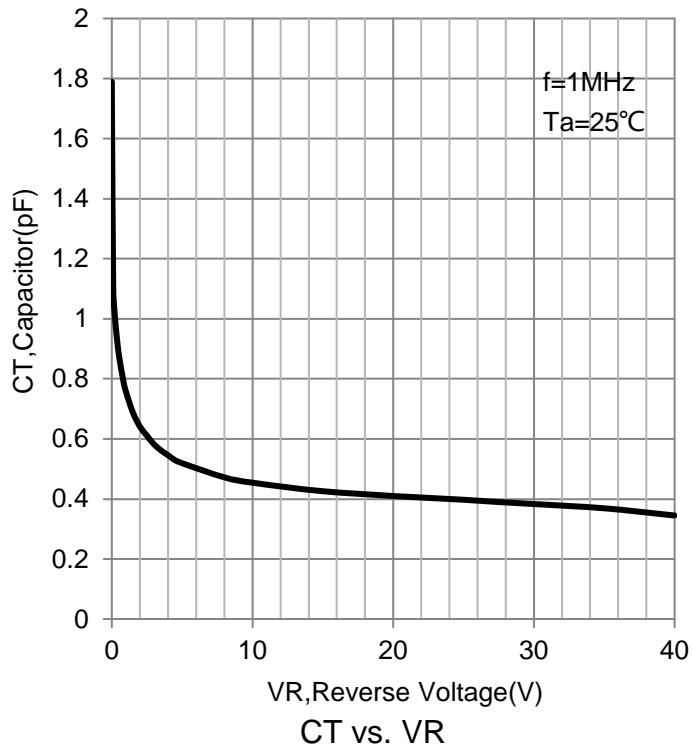
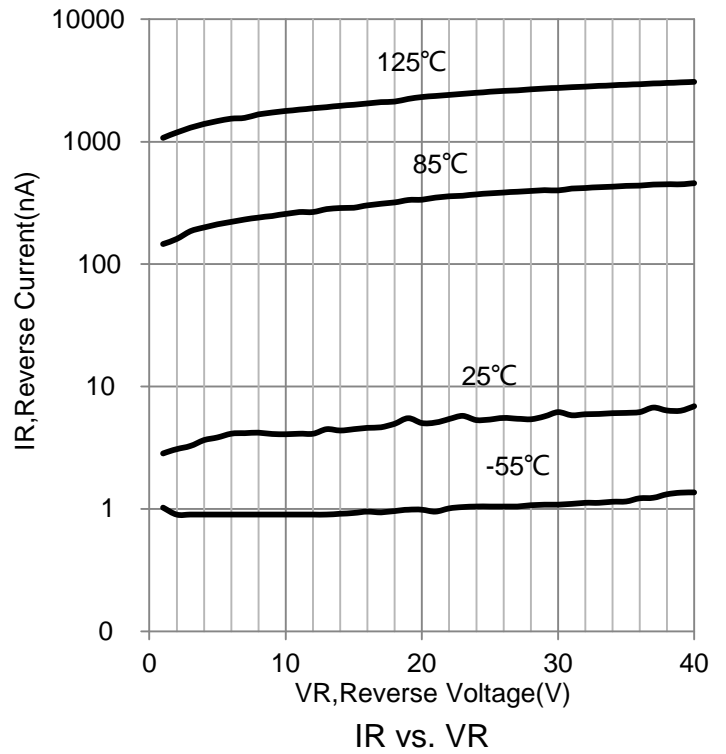
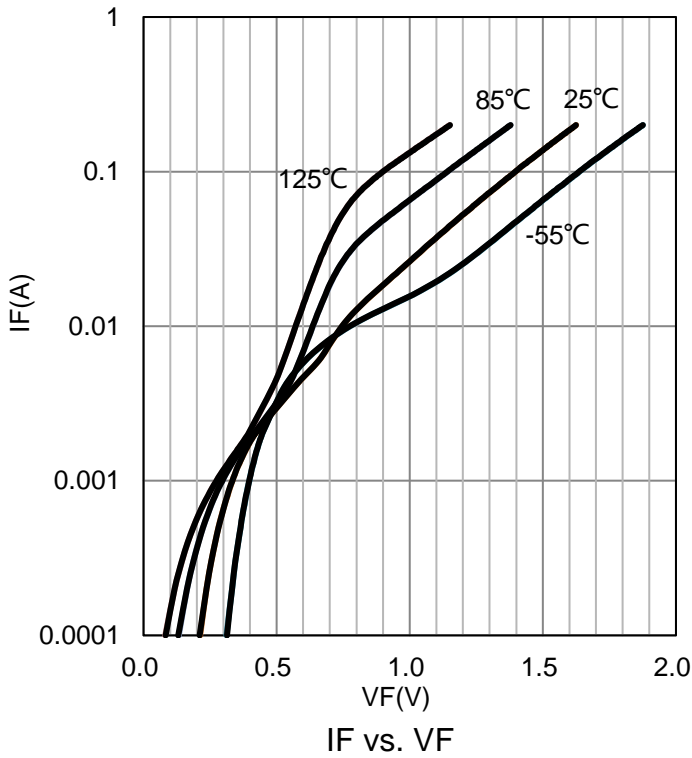
3. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limit	Unit
Peak reverse voltage	VRM	40	V
DC reverse voltage	VR	40	V
Mean rectifying current	IO	30	mA
Peak forward surge current	IFSM	200	mA
Thermal Resistance,Junction-to-Ambient	RθJA	400	°C/W
Thermal Resistance,Junction-to-Case	RθJC	250	°C/W
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-40~+125	°C

4. ELECTRICAL CHARACTERISTICS (Tj =25°C unless otherwise specified.)

Parameter	Symbol	Min	Typ.	Max	Unit
Forward voltage (IF =1mA)	VF	-	-	0.37	V
Reverse current (VR =10V)	IR	-	-	1	μA
Capacitance between terminals (VR =1V, f=1MHz)	CT	-	2	-	pF

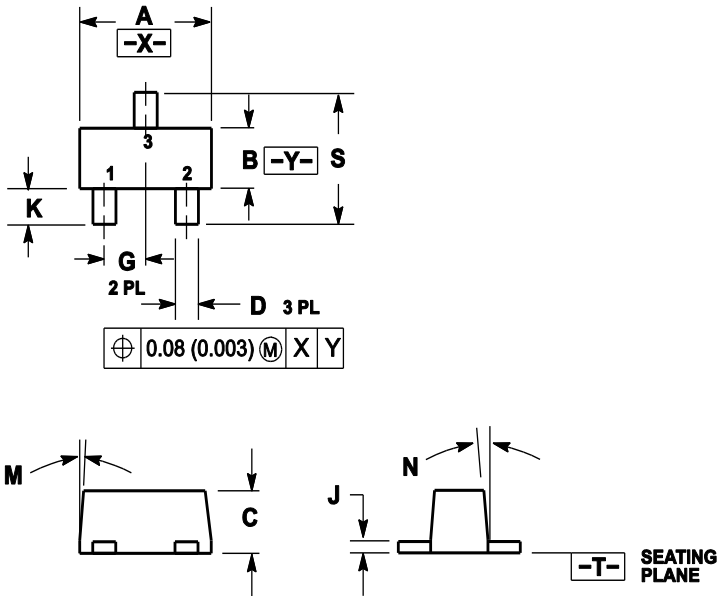
5 ELECTRICAL CHARACTERISTICS CURVES



6. OUTLINE AND DIMENSIONS

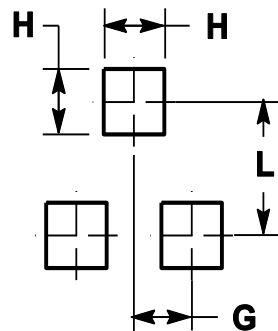
Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.60	1.70	0.059	0.063	0.067
B	0.75	0.85	0.95	0.030	0.034	0.040
C	0.60	0.70	0.80	0.024	0.028	0.031
D	0.23	0.28	0.33	0.009	0.011	0.013
G	0.50BSC			0.020BSC		
H	0.53REF			0.021REF		
J	0.10	0.15	0.20	0.004	0.006	0.008
K	0.30	0.40	0.50	0.012	0.016	0.02
L	1.10REF			0.043REF		
M	---	---	10°	---	---	10°
N	---	---	10°	---	---	10°
S	1.50	1.60	1.70	0.059	0.063	0.067

7. SOLDERING FOOTPRINT



单击下面可查看定价，库存，交付和生命周期等信息

[>>LRC\(乐山无线电\)](#)